

The documentation process conversion measures necessary to comply with this revision shall be completed by 12 January 1998

INCH-POUND

MIL-PRF-19500/601C
 12 October 1997
 SUPERSEDING
 MIL-PRF-19500/601B
 6 June 1997

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED (TOTAL DOSE ONLY)
 TRANSISTORS, N-CHANNEL, SILICON TYPES 2N7261 AND 2N7262 AND U SUFFIXES
 JANTXVR, F, G, AND H AND JANSR, F, G, AND H

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for an N-channel, enhancement-mode, MOSFET, radiation hardened (total dose only), power transistor. Two levels of product assurance are provided for each device type as specified in MIL-PRF-19500, with avalanche energy maximum rating (E_{AS}) and maximum avalanche current (I_{AS}).

1.2 Physical dimensions. See figure 1, TO-205AF and figure 2 (LCC).

1.3 Maximum ratings. Unless otherwise specified, T_A = +25°C.

Type	P _T 1/ 4/	P _T T _C = +25°C	V _{DS}	V _{DG}	V _{GS}	I _{D1} 2/ T _C = +25°C	I _{D2} T _C = +100°C	I _S 2/	I _{DM} 3/	T _{op} and T _{STG}	V _{ISO} 70,000 foot altitude
	<u>W</u>	<u>W</u>	<u>V dc</u>	<u>V dc</u>	<u>V dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A dc</u>	<u>A(pk)</u>	<u>°C</u>	<u>V dc</u>
2N7261	25	0.8	100	100	±20	8.0	5.0	8.0	32	-55 to	N/A
2N7262	25	0.8	200	200	±20	5.5	3.5	5.5	22	+150	N/A

1/ Derate linearly 0.2 W/°C for T_C > +25°C;

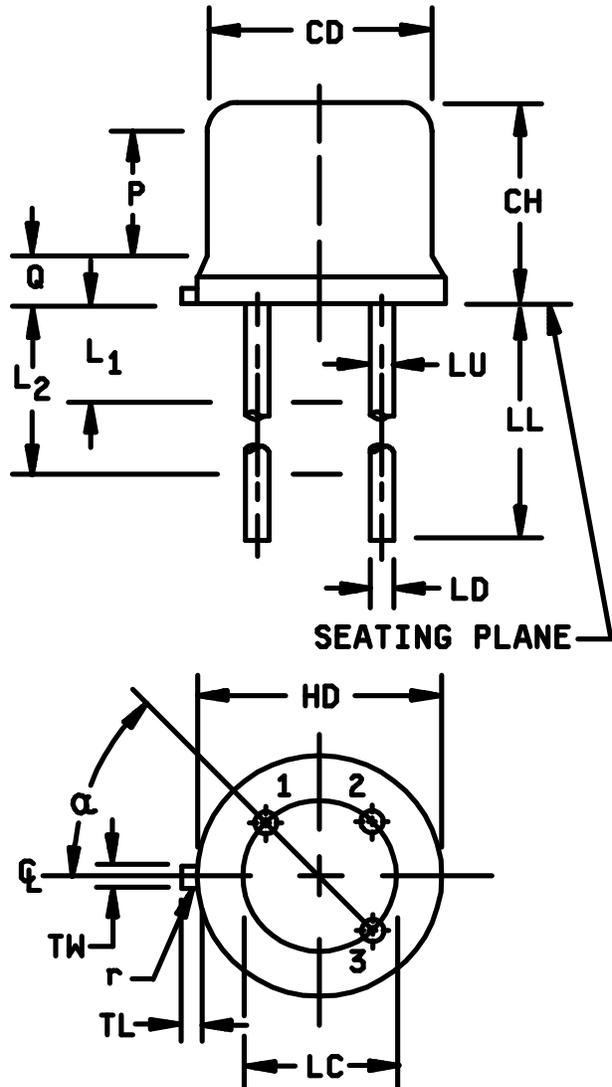
$$2/ I_D = \sqrt{\frac{T_J \text{ max} - T_C}{(R_{\theta JC})X(r_{Dson} \text{ at } T_J \text{ max})}}$$

3/ I_{DM} = 4 X I_{D1} as calculated in footnote 2/.

4/ Unless otherwise specified, electrical characteristics, ratings and conditions for "U" suffix devices (surface mount LCC) are identical to the corresponding non "U" suffix devices.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAT, 3990 East Broad Street, Columbus, OH 43216-5000, by using the Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

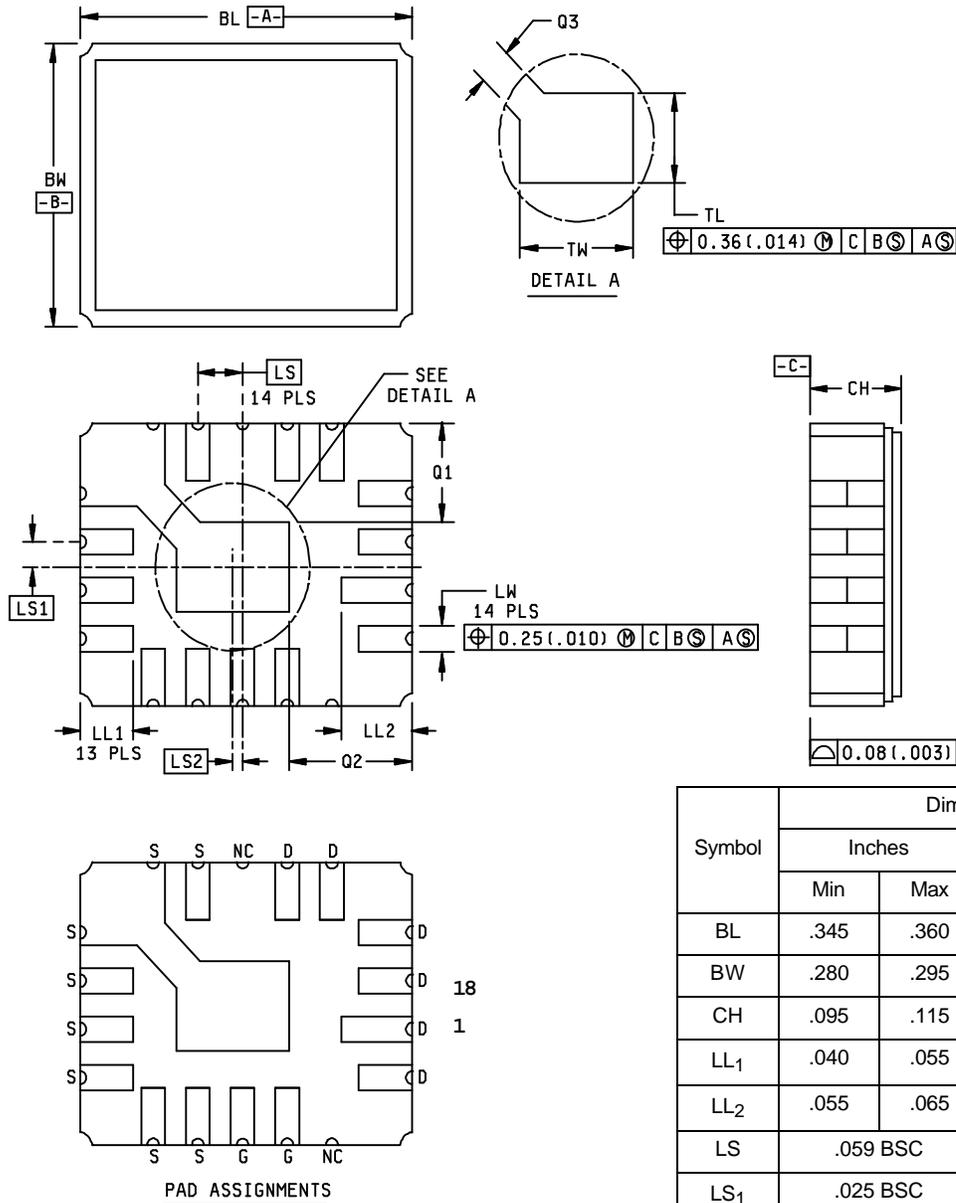
Symbol (see note 3)	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	.315	.355	8.01	9.01
CH	.160	.180	4.07	4.57
h	.009	.041	0.23	1.04
HD	.340	.370	8.64	9.39
LC	.200 BSC		5.08 BSC	
LD	.016	.021	0.41	0.53
LL	.500	.750	12.70	19.05
LU	.016	.019	0.41	0.48
L ₁	---	.050	---	1.27
L ₂	.250	---	6.35	---
P	.070	---	1.78	---
Q	---	.050	---	1.27
TL	.029	.045	0.74	1.14
TW	.028	.034	0.72	0.86
α	45° BSC			
Term 1	Source			
Term 2	Gate			
Term 3	Drain			



NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given in parentheses for general information only.
3. Refer to applicable symbol list.
4. The US Government preferred system of measurement is the metric SI system. However, this item was originally designed using inch-pound units of measurement. In the event of a conflict between the metric and inch-pound units, the inch-pound units shall take precedence.
5. Lead number 1 is the source, lead number 2 is the gate, lead number 4 is omitted from this outline. The drain is number 3 and is electrically connected to the case.

FIGURE 1. Physical dimensions for TO-205AF (2N7261 and 2N7262).



Symbol	Dimensions			
	Inches		Millimeters	
	Min	Max	Min	Max
BL	.345	.360	8.77	9.14
BW	.280	.295	7.12	7.49
CH	.095	.115	2.42	2.92
LL ₁	.040	.055	1.02	1.39
LL ₂	.055	.065	1.40	1.65
LS	.059 BSC		1.27 BSC	
LS ₁	.025 BSC		.635 BSC	
LS ₂	.008 BSC		.203 BSC	
LW	.020	.030	0.51	0.76
Q ₁	.105 REF		2.67 REF	
Q ₂	.120 REF		3.05 REF	
Q ₃	.045	.055	1.15	1.39
TL	.070	.080	1.78	2.03
TW	.120	.130	3.05	3.30

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Dimensions and tolerancing shall be in accordance with ANSI Y14.5M-1982.

FIGURE 2. Physical dimensions for LCC (2N7261U and 2N7262U).

1.4 Primary electrical characteristics at $T_C = +25^\circ\text{C}$.

Type	Min $V_{(BR)DSS}$ $V_{GS} = 0$ $I_D = 1.0$ mA dc	$V_{GS(TH)}$ $V_{DS} \geq V_{GS}$ $I_D = 1.0$ mA dc	Max I_{DSS1} $V_{GS} = 0$ $V_{DS} = 80$ percent of rated V_{DS}	Max $r_{DS(ON)}$ ^{1/} $V_{GS} = 12$ V dc		$R_{\theta JC}$ max	E_{AS} at I_{D1}	I_{AS}	
				$T_J = 25^\circ\text{C}$ at I_{D2}	$T_J = 150^\circ\text{C}$ at I_{D2}				
	<u>V dc</u>	<u>V dc</u>		<u>$\mu\text{A dc}$</u>	<u>ohm</u>	<u>ohm</u>	<u>$^\circ\text{C/W}$</u>	<u>mJ</u>	<u>A</u>
		Min	Max						
2N7261	100	2.0	4.0	25	0.180	0.390	5.0	130	8.0
2N7262	200	2.0	4.0	25	0.350	0.840	5.0	240	5.5

1/ Pulsed (see 4.5.1).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

MILITARY

MIL-STD-750 - Test Methods for Semiconductor Devices.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein (except for related associated specifications or specification sheets), the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Qualification. Devices furnished under this specification shall be products that are authorized by the qualifying activity for listing on the applicable qualified products list before contract award (see 4.2 and 6.3).

3.2 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500 and as follows.

I_{AS} - Rated avalanche current, nonrepetitive

3.3 Interface requirements and physical dimensions. The interface requirements and physical dimensions shall be as specified in MIL-PRF-19500 and on figures 1 (TO-205AF) and 2 (LCC) herein.

3.3.1 Lead material and finish. Lead material shall be Kovar or Alloy 52 for the TO - 205AF; a copper core or plated core is permitted. Lead finish shall be solderable as defined in MIL-PRF-19500, MIL-STD-750, and herein. Where a choice of lead material or finish is desired, it shall be specified in the acquisition document (see 6.5).

3.3.2 Internal construction. Multiple chip construction is not permitted to meet the requirements of this specification.

3.4 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.5 Electrostatic discharge protection. The devices covered by this specification require electrostatic discharge protection.

3.5.1 Handling. MOS devices must be handled with certain precautions to avoid damage due to the accumulation of static charge. However, the following handling practices are recommended (see 3.5).

- a. Devices should be handled on benches with conductive handling devices.
- b. Ground test equipment, tools, and personnel handling devices.
- c. Do not handle devices by the leads.
- d. Store devices in conductive foam or carriers.
- e. Avoid use of plastic, rubber, or silk in MOS areas.
- f. Maintain relative humidity above 50 percent if practical.
- g. Care should be exercised during test and troubleshooting to apply not more than maximum rated voltage to any lead.
- h. Gate must be terminated to source, $R \leq 100$ k, whenever bias voltage is to be applied drain to source.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in 4.4.2 and 4.4.3 herein.

4. VERIFICATION

4.1 Classification of inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3)
- c. Conformance inspection (see 4.4).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500.

4.2.1 Group E inspection. Group E inspection shall be conducted in accordance with MIL-PRF-19500 and table III herein.

4.3 Screening (JANS, JANTX and JANTXV levels only). Screening shall be in accordance with MIL-PRF-19500 (Appendix E, table IV), and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see appendix E, table IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTXV level
<u>1</u> /	Method 3470 (see 4.5.4)	Method 3470 (see 4.5.4)
<u>1</u> /	Method 3161 (see 4.5.3)	Method 3161 (see 4.5.3)
<u>1</u> /	Gate stress test (see 4.5.5)	Gate stress test (see 4.5.5)
9 <u>1</u> /	Subgroup 2 of table I herein; I _{GSS} , I _{DSS1}	Subgroup 2 of table I herein
10	MIL-STD-750, method 1042, test condition B	MIL-STD-750, method 1042, test condition B
11	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(on)} , V _{GS(TH)} Subgroup 2 of table I herein; $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater.	I _{GSSF1} , I _{GSSR1} , I _{DSS1} , r _{DS(on)} , V _{GS(TH)} Subgroup 2 of table I herein
12	MIL-STD-750, method 1042; test condition A	MIL-STD-750, method 1042; test condition A
13	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value	Subgroups 2 and 3 of table I herein $\Delta I_{GSSF1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{GSSR1} = \pm 20$ nA dc or ± 100 percent of initial value, whichever is greater. $\Delta I_{DSS1} = \pm 10$ μ A dc or ± 100 percent of initial value, whichever is greater. $\Delta r_{DS(on)1} = \pm 20$ percent of initial value $\Delta V_{GS(TH)1} = \pm 20$ percent of initial value

1/ Shall be performed anytime before screen 10.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500, and as specified herein. Alternate flow is allowed for quality conformance inspection in accordance with appendix E of MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with appendix E, table V of MIL-PRF-19500. End-point electrical measurements shall be in accordance with table I, group A, subgroup 2 herein.

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table VIa (JANS) and table VIb (JANTX and JANTXV) of MIL-PRF-19500, and herein. Electrical measurements (end-points) and delta requirements shall be in accordance with table I, group A, subgroup 2 herein.

4.4.2.1 Group B inspection, appendix E, table VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B3	1051	Test condition G, 100 cycles.
B3	2075	See 3.3.2.
B3	2077	Scanning electron microscope (SEM) qualification may be performed anytime prior to lot formation.
B3	2037	Test condition A, all internal wired for each device shall be pulled separately.
B4	1042	Condition D, 2,000 cycles. No heat sink nor forced-air cooling on the device shall be permitted during the on cycle. The heating cycle shall be 30 seconds minimum.
B5	1042	Test condition A, $V_{DS} = \text{rated}$ $T_A = +175^\circ\text{C}$, $t = 120$ hours.
B5	1042	Condition B, $V_{GS} = \text{rated}$; $T_A = 175^\circ\text{C}$; $t = 24$ hours.
B5	2037	Bond strength (Al-Au die interconnects only); test condition A.
B6	3161	See 4.5.2.

4.4.2.2 Group B inspection, appendix E, table VIb (JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	1051	Test condition G, 25 cycles.
B3	1042	Test condition D, 2,000 cycles; The heating cycle shall be 30 seconds minimum.
B4	2075	See 3.3.2.
B4	2037	Test condition A. All internal bond wires for each device shall be pulled separately.
B5 and B6		Not applicable.

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable of table I, group A, subgroup 2 herein.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
C2	1056	Test condition B.
C2	2036	Test condition A; weight = 10 pounds; t = 15 s (applicable to TO - 205AF only).
C2	1021	Omit initial conditioning.
C5	1001	Test condition C. For device type 2N7270: $V_{DS} = 500 \text{ V}$; $I_{(ISO)} < 0.25 \text{ mA}$.
C6	1042	Test condition D, 6,000 cycles. The heating cycle shall be 30 seconds minimum.

4.4.4 Group D Inspection. Group D inspection shall be conducted in accordance with appendix E, table VIII of MIL-PRF-19500 and table II herein.

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Thermal resistance. Thermal resistance measurements shall be performed in accordance with method 3161 of MIL-STD-750. The maximum limit of $R_{\theta JC(max)} = 5.0^{\circ}\text{C/W}$. The following parameter measurements shall apply:

- a. Measuring current (I_M) 10 mA.
- b. Drain heating current (I_H) 1 A (1.3 A minimum for LCC).
- c. Heating time (t_H) Steady-state (see MIL-STD-750, method 3161 for definition).
- d. Drain-source heating voltage (V_H) 25 V (15 V for LCC).
- e. Measurement time delay (t_{MD}) 30 μs to 60 μs .
- f. Sample window time (t_{SW}) 10 μs maximum.

4.5.3 Thermal impedance ($Z_{\theta JC}$ measurements). The $Z_{\theta JC}$ measurements shall be performed in accordance with MIL-STD-750, method 3161. The maximum limit (not to exceed figure 3, thermal impedance curves and the group A, subgroup 2 limits) for $Z_{\theta JC}$ in screening (appendix E, table IV of MIL-PRF-19500) shall be derived by each vendor by means of statistical process control. When the process has exhibited control and capability, the capability data shall be used to establish the fixed screening limit. In addition to screening, once a fixed limit has been established, monitor all future sealing lots using a random five piece sample from each lot to be plotted on the applicable X, R chart. If a lot exhibits an out of control condition, the entire lot shall be removed from the line and held for Engineering evaluation and disposition. This procedure may be used in lieu of an in line procedure.

- a. Measuring current (I_M) 10 mA.
- b. Drain heating current (I_H) 1 A minimum (1.3 A minimum for LCC)..
- c. Heating time (t_H) 10 ms.
- d. Drain-source heating voltage (V_H)- 25 V (15 V for LCC).
- e. Measurement time delay (t_{MD}) 30 μs to 60 μs .
- f. Sample window time (t_{SW}) 10 μs maximum.

4.5.4 Single pulse avalanche energy (E_{AS}).

- a. Peak current (I_{AS}) $I_{AS(max)}$
- b. Peak gate voltage (V_{GS}) 10 V.
- c. Gate to source resistor (R_{GS}) $25\Omega \leq R_{GS} \leq 200\Omega$.
- d. Initial case temperature (T_C) $+25^\circ\text{C} +10^\circ\text{C}, -5^\circ\text{C}$.
- e. Inductance (L) $\left[\frac{2E_{AS}}{(I_{DI})^2} \right] \left[\frac{(V_{BR} - V_{DD})}{V_{BR}} \right] \text{ mH minimum}$
- f. Number of pulses to be applied 1 pulse minimum.
- g. Supply voltage (V_{DD}) 25 V for 2N7261, 50 V for 2N7262

4.5.5 Gate stress test.

- a. $V_{GS} = 30 \text{ V minimum}$.
- b. $t = 250 \mu\text{s minimum}$

TABLE I. Group A inspection.

Inspection <u>1</u> /	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Thermal impedance <u>2</u> /	3161	See 4.5.3	$Z_{\theta JC}$		1.40	°C/W
Breakdown voltage, drain to source	3407	$V_{GS} = 0$ V dc, $I_D = 1$ mA dc, bias condition C	$V_{(BR)DSS}$			
2N7261 2N7262				100 200		V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}$ $I_D = 1$ mA dc	$V_{GS(TH)1}$	2.0	4.0	V dc
Gate current	3411	$V_{GS} = +20$ V dc and -20 V dc, bias condition C, $V_{DS} = 0$	$I_{GSS(TH)1}$		± 100	nA dc
Drain current	3413	$V_{GS} = 0$ V dc, bias condition C, $V_{DS} = 80$ percent of rated V_{DS}	I_{DSS1}		25	μ A dc
Static drain to source on-state resistance	3421	$V_{GS} = 12$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(on)1}$			
2N7261 2N7262					0.180 0.350	ohm ohm
Static drain to source on-state resistance	3421	$V_{GS} = 12$ V dc, condition A, pulsed (see 4.5.1), $I_D = I_{D1}$	$r_{DS(on)2}$			
2N7261 2N7262					0.185 0.364	ohm ohm
Forward voltage	4011	Pulsed (see 4.5.1), $I_D = I_{D1}$, $V_{GS} = 0$ V dc	V_{SD}			
2N7261 2N7262					1.5 1.4	V V

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 3</u>						
High-temperature operation:						
Gate current	3411	$T_C = T_J = +125^\circ\text{C}$ $V_{GS} = +20\text{ V dc and } -20\text{ V dc,}$ bias condition C, $V_{DS} = 0$	I_{GSS2}		± 200	nA dc
Drain current	3413	$V_{GS} = 0\text{ V dc, bias condition C,}$ $V_{DS} = 100\text{ percent of rated } V_{DS}$ $V_{DS} = 80\text{ percent of rated } V_{DS}$	I_{DSS2}		1.0	mA dc
			I_{DSS3}		0.25	mA dc
Static drain to source on-state resistance	3421	$V_{GS} = 12\text{ V dc,}$ pulsed (see 4.5.1), $I_D = I_{D2}$	$r_{DS(on)3}$			
2N7261 2N7262					0.350 0.6	ohm ohm
Gate to source voltage (thresholds)	3403	$V_{DS} \geq V_{GS}, I_D = 1\text{ mA dc}$	$V_{GS(TH)2}$	1.0		V dc
Low-temperature operation:						
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS}, I_D = 1\text{ mA dc}$	$V_{GS(TH)3}$		5.0	V dc
<u>Subgroup 4</u>						
Forward transconductance	3475	$I_D = \text{rated } I_{D2}, V_{DD} = 15\text{ V (see 4.5.1)}$	gFS			
2N7261 2N7262				2.5 2.5		S S
Switching time test	3472	$I_D = I_{D1}, V_{GS} = 12\text{ V dc,}$ $R_G = 2.35\Omega, V_{DD} = 50\text{ percent}$ of rated V_{DS}				
Turn-on delay time			$t_{d(on)}$			
2N7261 2N7262					25 25	ns ns

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 4</u> - Continued						
Rise time			t_r			
2N7261					55	ns
2N7262					40	ns
Turn-off delay time			$t_d(\text{off})$			
2N7261					55	ns
2N7262					60	ns
Fall time			t_f			
2N7261					45	ns
2N7262					45	ns
<u>Subgroup 5</u>						
Safe operating area test (high voltage)	3474	See figure 5 and 5; $t_p = 10$ ms minimum, $V_{DS} = 80$ percent of maximum rated V_{DS} , ($V_{DS} \leq 200$)				
Electrical measurements		See table I, subgroup 2 herein.				
<u>Subgroup 6</u>						
Not applicable						
<u>Subgroup 7</u>						
Gate charge	3471	Condition B				
On-state gate charge			$Q_{G(\text{on})}$			
2N7261					50	nC
2N7262					50	nC
Gate to source charge			Q_{GS}			
2N7261					12	nC
2N7262					10	nC

See footnote at end of table.

TABLE I. Group A inspection - Continued.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 7</u> - Continued						
Gate to drain charge 2N7261 2N7262			Q_{GD}		20 25	nC nC
Reverse recovery time 2N7261 2N7262	3473	$d_i/d_t \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq 30 \text{ V}$, $I_D = I_{D1}$	t_{rr}		350 400	ns ns

1/ For sampling plan, see MIL-PRF-19500.

2/ This test is required for the following endpoint measurements only (not intended for screen 13):

JANS - group B, subgroups 3 and 4.

JANTX and JANTXV - group B, subgroups 2 and 3;
group C, subgroup 6;
group E, subgroup 1.

TABLE II. Group D inspection.

Inspection 1/ 2/ 5/	MIL-STD-750		Symbol	Pre-irradiation limits				Post-irradiation limits				Unit
	Method	Conditions		R		F, G, and H		R		F, G, and H		
				Min	Max	Min	Max	Min	Max	Min	Max	
<u>Subgroup 1</u>												
Not applicable												
<u>Subgroup 2</u>		$T_C = +25^\circ\text{C}$										
Steady-state total dose irradiation (V_{GS} bias) 4/	1019	$V_{GS} = 12\text{ V},$ $V_{DS} = 0$										
Steady-state total dose irradiation (V_{DS} bias) 4/	1019	$V_{GS} = 0,$ $V_{DS} = 80$ percent of rated V_{DS} (preirradiation)										
End-point electrical												
Breakdown voltage, drain to source	3407	$V_{GS} = 0,$ $I_D = 1\text{ mA},$ bias condition C	V_{BRDSS}									
2N7261 2N7262				100 200		100 200		100 200		100 200		V dc V dc
Gate to source voltage (threshold)	3403	$V_{DS} \geq V_{GS},$ $I_D = 1\text{ mA}$	V_{GSth}									
2N7261 2N7262				2 2	4 4	2 2	4 4	2 2	4 4	1.25 1.25	4.50 4.50	V dc V dc
Gate current	3411	$V_{GS} = 20\text{ V},$ $V_{DS} = 0,$ bias condition C	I_{GSSF1}		100		100		100		100	nA dc
Gate current	3411	$V_{GS} = -20\text{ V},$ $V_{DS} = 0,$ bias condition C	I_{GSSR1}		-100		-100		-100		-100	nA dc

See footnotes at end of table.

TABLE II. Group D inspection - Continued.

Inspection 1/ 2/ 5/	MIL-STD-750		Symbol	Pre-irradiation limits				Post-irradiation limits				Unit
	Method	Conditions		R		F, G, and H		R		F, G, and H		
				Min	Max	Min	Max	Min	Max	Min	Max	
Subgroup 2 - Continued	3413	V _{GS} = 0 Bias condition C V _{DS} = 80 percent of rated V _{DS} (preirradiation)	I _{DSS}									
				2N7261 2N7262	25 25	25 25	25 25	50 50	μA dc μA dc			
Static drain to source on-state voltage	3405	V _{GS} = 12 V Condition A pulsed (see 4.51) I _D = I _{D2}	V _{DSon1}									
				2N7261 2N7262	0.9 1.225	0.9 1.225	0.9 1.225	1.2 1.68	V dc V dc			
Forward voltage source drain diode	4011	V _{GS} = 0 V I _D = I _{D1}	V _{SD}									
				2N7261 2N7262	1.5 1.4	1.5 1.4	1.5 1.4	1.5 1.4	V dc V dc			

1/ For sampling plan, see MIL-PRF-19500.

2/ Group D qualification may be performed anytime prior to lot formation. Wafers qualified to these group D QCI requirements may be used for any other detail specification utilizing the same die design.

3/ The F designation represent devices which pass endpoints at both 100K and 300K rad (Si). The G designation represents devices which pass 100K, 300K, and 600K rad (Si) endpoints. The H designation represents devices which pass 100k, 300k, 600k and 1000k rad (Si)

4/ Separate samples shall be pulled for each bias.

5/ At the manufacturers option, group D samples need not be subjected to the screening tests, and may be assembled in it's qualified package or in any qualified package that the manufacturer has data to correlate the performance to the designated package.

TABLE III. Group E inspection (all quality levels) for qualification only.

Inspection	MIL-STD-750		Qualification and large lot quality conformance inspection
	Method	Conditions	
<u>Subgroup 1</u>			12 devices c = 0
Thermal shock (temperature cycling)	1051	Test condition G, 500 cycles	
Hermetic seal	1071		
Fine leak Gross leak			
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 2</u> ^{1/}			12 devices c = 0
Steady-state reverse bias	1042	Condition B, 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
Steady-state gate bias	1042	Condition A, 1,000 hours	
Electrical measurements		See table I, group A, subgroup 2	
<u>Subgroup 3</u>			
Not applicable			
<u>Subgroup 4</u>			12 devices c = 0
Thermal resistance	3161	$R_{\theta JC} = 5.0 \text{ }^\circ\text{C/W}$ maximum. See 4.5.2	

^{1/} A separate sample for each test shall be pulled.

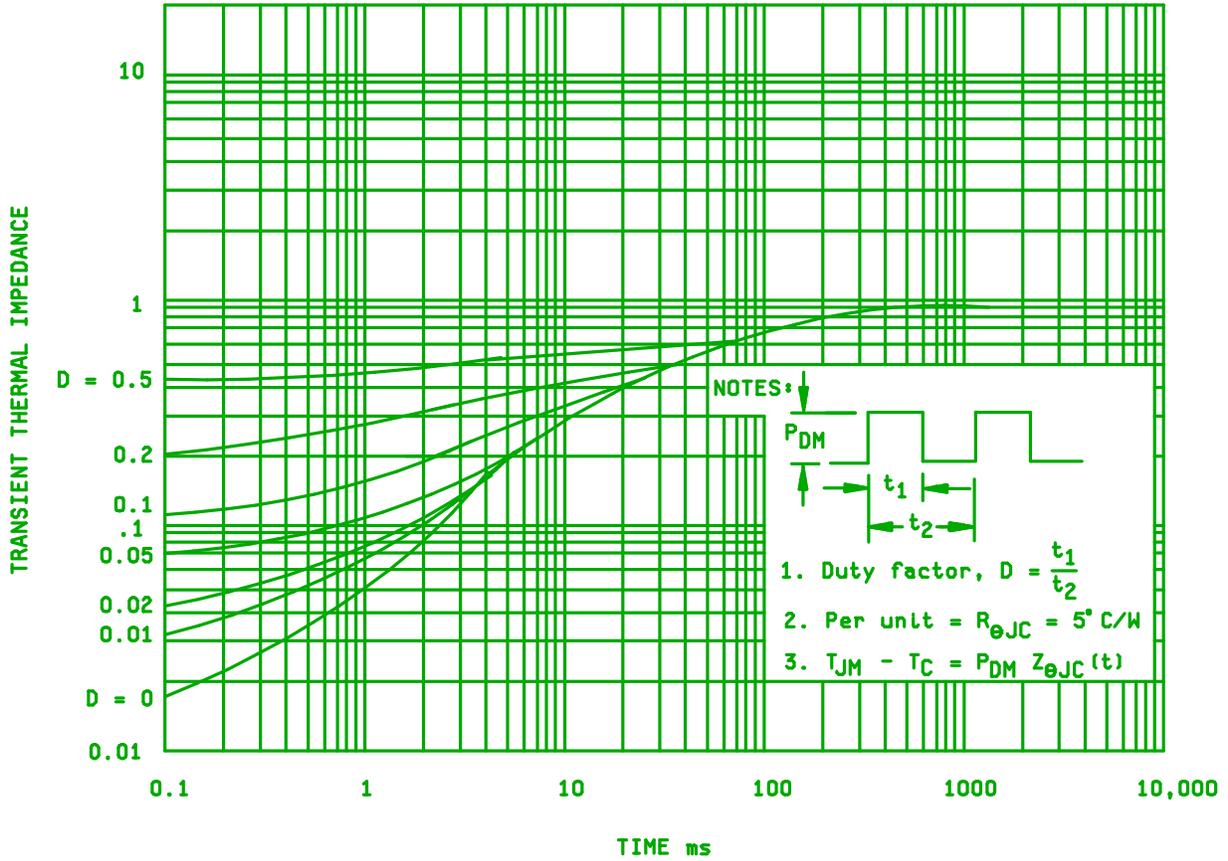


FIGURE 3. Thermal impedance curves.

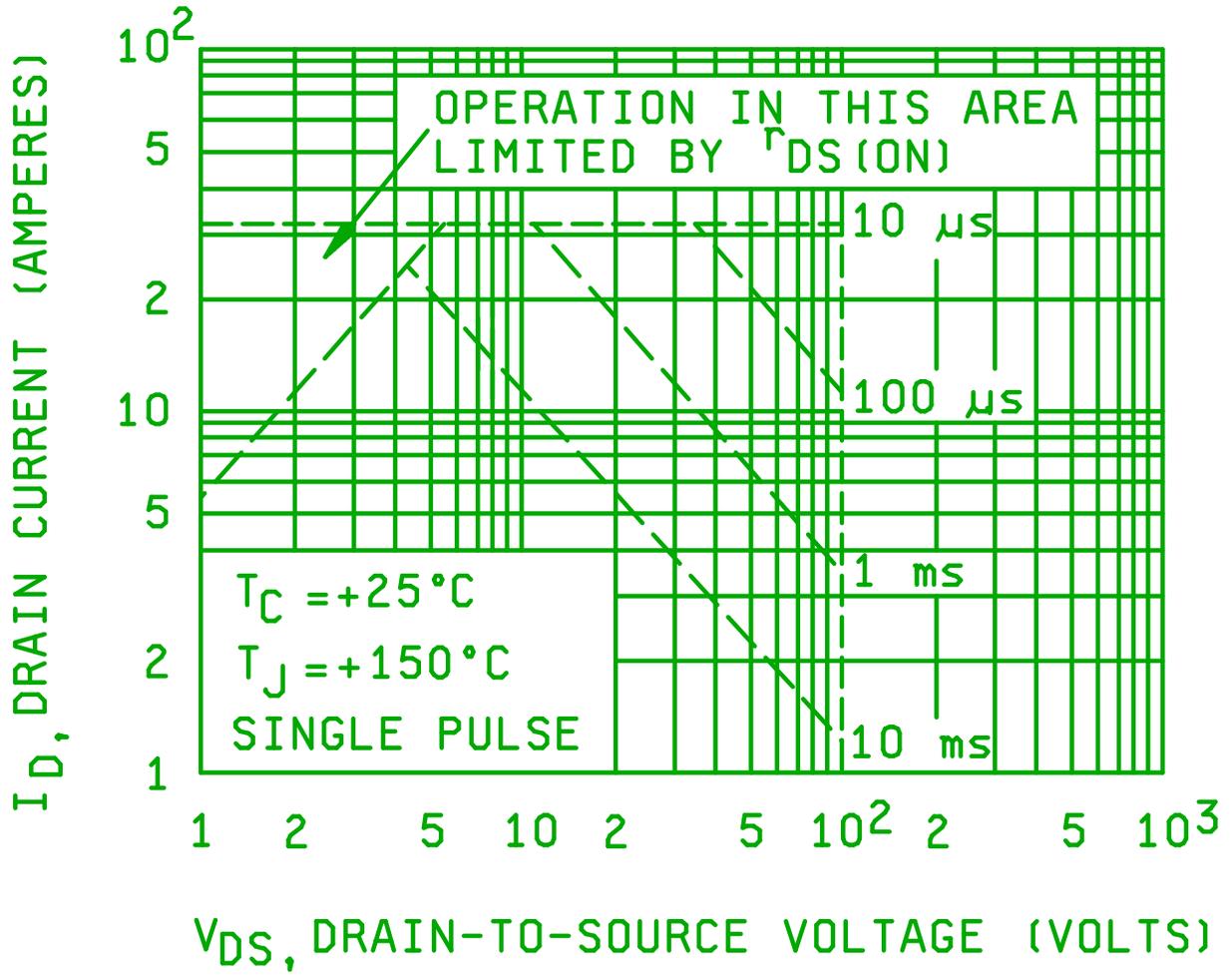


FIGURE 4. Safe operating area graph.

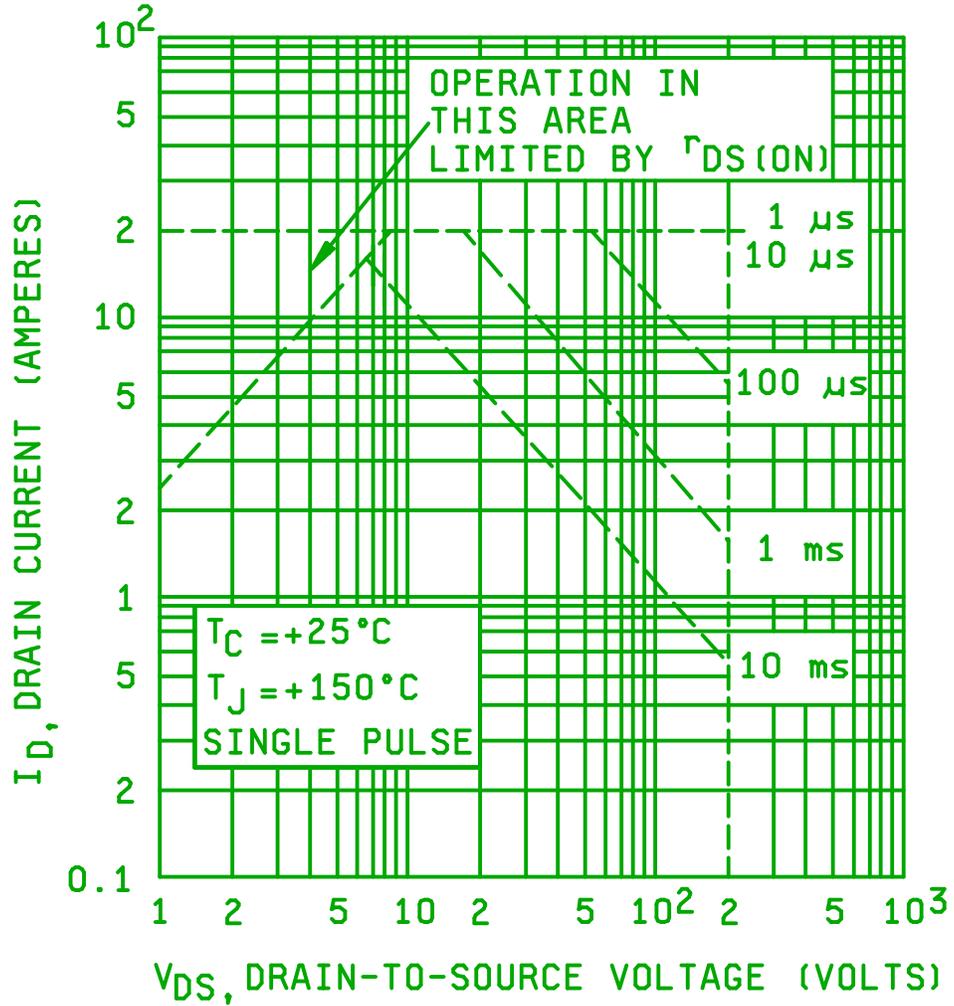


FIGURE 5. Safe operating area graph.

5. PACKAGING

5.1 Packaging. Packaging shall prevent mechanical damage of the devices during shipping and handling and shall not be detrimental to the device. When actual packaging of material is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Points' packaging activity within the Military Department or Defense Agency, or within the Military Departments' System Command. Packaging data retrieval is available from the managing Military Departments' or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

5.2 Marking. Unless otherwise specified (see 6.2), marking shall be in accordance with MIL-STD-129.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory.)

6.1 Notes. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. See MIL-PRF-19500.

6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Products List QPL No.19500 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center Columbus, ATTN: DSCC-VQE, 3990 East Broad Street, Columbus, OH 43216-5000.

6.4 Substitution information. Devices covered by this specification are substitutable for the manufacturer's and user's Part or Identifying Number (PIN). This information in no way implies that manufacturer's PIN's are suitable for the military PIN.

Preferred types	Commercial types	
	TO-205AF	LCC
2N7261, U	IRHFX130 <u>1/</u>	IRHEX130 <u>1/</u>
2N7262, U	IRHFX230 <u>1/</u>	IRHEX230 <u>1/</u>

1/ Replace "X" with number indicating qualified Rad Hardness follows:

- 7 = 100K Rad Si
- 3 = 300K Rad Si
- 4 = 600K Rad Si
- 8 = 1000K Rad Si

6.5 Ordering data. Acquisition documents may specify the material and finish (see 3.3.1).

6.6 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

MIL-PRF-19500/601C

Custodians:

Army - CR
Navy - EC
Air Force - 17
NASA - NA

Preparing activity:

DLA - CC

(Project 5961-1949)

Review activities:

Air Force - 19, 70, 80

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

I RECOMMEND A CHANGE:	1. DOCUMENT NUMBER MIL-PRF-19500/601C	2. DOCUMENT DATE (YYMMDD) 971012
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3. DOCUMENT TITLE SEMICONDUCTOR DEVICE, FIELD EFFECT RADIATION HARDENED (TOTAL DOSE ONLY) TRANSISTOR, N-CHANNEL, SILICON TYPES 2N7261 AND 2N7262, JANTXVR, F, G, AND H, AND JANSR, F, G, AND H

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)	b. ORGANIZATION	
c. ADDRESS (Include Zip Code)	d. TELEPHONE (Include Area Code) (1) Commercial (2) AUTOVON (If applicable)	7. DATE SUBMITTED (YYMMDD)

8. PREPARING ACTIVITY

a. NAME Alan Barone	b. TELEPHONE (Include Area Code) (1) Commercial (614)692-0510 (2) AUTOVON 850-0510	
c. ADDRESS (Include Zip Code) from Defense Supply Center Columbus, ATTN: DSCC-VAT, 3990 East Broad Street, Columbus, OH 43216-5000	IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT: Defense Quality and Standardization Office 5203 Leesburg Pike, Suite 1403, Falls Church, VA 22041-3466 Telephone (703) 756-2340 AUTOVON 289-2340	